

ABSTRACT**SUPPORT FOR A SEMICONDUCTOR STRUCTURE**

The invention relates to a support (1) for a semiconductor structure comprising a charge-trapping layer (2) on a base substrate (3). The trapping layer (2) consists of a polycrystalline main layer (2a) and, interposed in the main layer (2a) or between the main layer (2a) and the base substrate (3), at least one intermediate polycrystalline layer (2b) composed of a silicon and carbon alloy or carbon, the intermediate layer (2b) having a resistivity greater than 1000 ohm.cm.

Figure 1